







TPS65235-1 SLVSDP1F - JANUARY 2017 - REVISED MAY 2023

TPS65235-1 LNB Voltage Regulator With I²C Interface

1 Features

- Complete integrated solution for LNB and I²C interface
- DiSEqC 2.x, and DiSEqC 1.x compatible
- Supports 5-V, 12-V, and 15-V power rail
- Up to 1000-mA accurate output current limit adjustable by external resistor
- Boost switch peak current limit proportional to LDO current limit
- Boost converter with 140-m Ω low $R_{ds(on)}$ internal power switch
- Boost switching frequency 1-MHz or 500-kHz selectable
- Audible noise avoided at force PWM mode
- Dedicated enable pin for non-I²C application
- Low-dropout (LDO) regulator with push-pull output stage for VLNB output
- Built-in accurate 22-kHz tone generator and external tone input support
- Supports both external 44-kHz and 22-kHz tone
- Adjustable soft start and 13-V to 18-V voltage transition time
- 650-mV to 750-mV 22-kHz tone amplitude selection
- I²C registers accessible with EN low
- Short circuit dynamic protection
- Diagnostics for output voltage level, DiSEqC tone input and output, current level, and cable connection
- Thermal protection available
- 20-pin WQFN 3-mm × 3-mm (RUK) package

2 Applications

- Set top box satellite receiver
- TV satellite receiver
- PC card satellite receiver
- Satellite TV

3 Description

Designed for analog and digital satellite receivers, the TPS65235-1 is a monolithic voltage regulator with I²C interface; specifically to provide the 13-V to 18-V power supply and the 22-kHz tone signal to the LNB down converter in the antenna dish or to the multi-switch box. The device offers a complete solution with minimum component count, low power dissipation together with simple design and I²C standard interface.

The TPS65235-1 features high power efficiency. The boost converter integrates a 140-mΩ power MOSFET running at 1-MHz or 500-kHz selectable switching frequency. Drop out voltage at the linear regulator is 0.8 V to minimize power loss. The TPS65235-1 provides multiple ways to generate the 22-kHz signal. Integrated linear regulator with push-pull output stage generates 22-kHz tone signal superimposed at the output even at zero loading. Current limit of linear regulator can be programmed by external resistor with ±10% accuracy. Full range of diagnostic read by I²C is available for system monitoring.

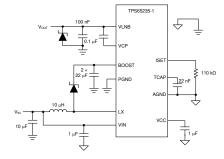
The TPS65235-1 has a special design at FCCM mode to avoid the audible noise especially when VIN is higher or closer to the VLNB output.

The TPS65235-1 supports advanced DiSEqC 2.x standard with 22-kHz tone detection circuit and output interface.

Package Information⁽¹⁾

| PART NUMBER | | PACKAGE | BODY SIZE (NOM) | | | |
|-------------|------------|----------------|-------------------|--|--|--|
| | TPS65235-1 | RUK (WQFN, 20) | 3.00 mm × 3.00 mm | | | |

For all available packages, see the orderable addendum at the end of the data sheet.



Simplified Schematic

1 Features......1



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5 Pin Configuration and Functions

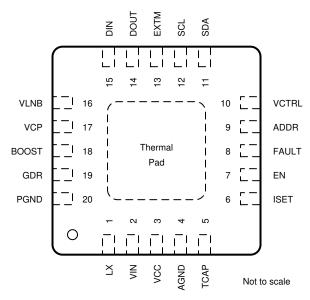


Figure 5-1. RUK Package 20-Pin WQFN With Exposed Thermal Pad Top View

Table 5-1. Pin Functions

| NO. NAME | | TYPE ⁽¹⁾ | DESCRIPTION | |
|----------|-------------|---------------------|---|--|
| | | ITPE | DESCRIPTION | |
| 1 | LX | I | Switching node of the boost converter | |
| 2 | VIN | S | nput of internal linear regulator | |
| 3 | VCC | 0 | nternal 6.3-V power supply. Connect a 1- μ F ceramic capacitor from this pin to ground. When V_{IN} is 5 connect the VCC pin to the VIN pin. | |
| 4 | AGND | S | Analog ground. Connect all ground pins and power pad together. | |
| 5 | TCAP | 0 | Connect a capacitor to this pin to set the rise time of the LNB output. | |
| 6 | ISET | 0 | Connect a resistor to this pin to set the LNB output current limit. | |
| 7 | EN | I | Enable this pin to enable the VLNB output. pull this pin to ground to disable the output. The output is then pulled to ground, and, when the EN pin is low, the I ² C interface can be accessed. | |
| 8 | FAULT | 0 | Open drain output pin, it goes low if any fault flag is set. | |
| 9 | ADDR | I | Connect a different resistor to this pin to set different I ² C addresses (see the Table 7-4 table). | |
| 10 | VCTRL | I | Voltage level at this pin to set the output voltage (see the Table 7-3). | |
| 11 | SDA | I/O | I ² C compatible bidirectional data | |
| 12 | SCL | I | I ² C compatible clock input | |
| 13 | EXTM | I | External modulation logic input pin that activates the 22-kHz tone output. The feeding signal can be 22-kHz tone or logic high or low. | |
| 14 | DOUT | 0 | Tone detection output | |
| 15 | DIN | I | Tone detection input | |
| 16 | VLNB | 0 | Output of the power supply connected to satellite receiver or switch | |
| 17 | VCP | 0 | Gate drive supply voltage and output of charge pump. Connect a capacitor between this pin and the VLNB pin. | |
| 18 | BOOST | 0 | Output of the boost regulator and Input voltage of the internal linear regulator | |
| 19 | GDR | 0 | Control the gate of the external MOSFET for DiSEqc 2.x support | |
| 20 | PGND | S | Power ground for the boost converter | |
| _ | Thermal Pad | _ | The thermal pad must be soldered to the printed circuit board (PCB) for optimal thermal performance. Use thermal vias on the PCB to enhance power dissipation. | |

(1) I = input, O = output, I/O = input and output, S = power supply



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

| | | MIN | MAX | UNIT |
|--|--|------|-----|------|
| | VIN, LX, BOOST, VLNB | 1 | 30 | |
| | VCP, GDR (referenced to VLNB pin) | | 7 | |
| Voltage | VCC, EN, ADDR, FAULT, SCL, SDA, VCTRL, EXTM, DOUT, DIN, TCAP | -0.3 | 7 | V |
| | ISET | -0.3 | 3.6 | |
| | PGND | -0.3 | 0.3 | |
| Operating junction temperature, T _J | | -40 | 150 | °C |
| Storage temperature, T _{stg} | | -55 | 150 | |

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

| | | | VALUE | UNIT |
|-----------------|--------------------------|--|-------|------|
| | | Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾ | ±4000 | V |
| V _{(E} | ^{SD)} discharge | Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾ | ±1500 | V |

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

| | | MIN | NOM MAX | UNIT |
|-----------------|--------------------------------|-----|---------|------|
| V _{IN} | Input operating voltage | 4.5 | 20 | V |
| T _A | Operating junction temperature | -40 | 125 | °C |

6.4 Thermal Information

| | | TPS65235-1 | |
|------------------------|--|------------|------|
| | THERMAL METRIC ⁽¹⁾ | RUK (WQFN) | UNIT |
| | | 20 PINS | |
| $R_{\theta JA}$ | Junction-to-ambient thermal resistance | 44.8 | °C/W |
| R _{0JC(top)} | Junction-to-case (top) thermal resistance | 47.3 | °C/W |
| $R_{\theta JB}$ | Junction-to-board thermal resistance | 16.5 | °C/W |
| Ψ_{JT} | Junction-to-top characterization parameter | 0.5 | °C/W |
| ΨЈВ | Junction-to-board characterization parameter | 16.4 | °C/W |
| R ₀ JC(bot) | Junction-to-case (bottom) thermal resistance | 3.6 | °C/W |

 For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



6.5 Electrical Characteristics

-40°C \leq T_J \leq 125°C, V_{IN} = 12 V, f_{SW} = 1 MHz (unless otherwise noted)

| | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|----------------------------|--|---|-------|------|-------|------|
| INPUT SUPI | PLY | | | | | |
| V _{IN} | Input voltage range | | 4.5 | 12 | 20 | V |
| I _{DD(SDN)} | Shutdown supply current | EN = 0b | 90 | 120 | 150 | μA |
| I _{LDO(Q)} | LDO quiescent current | EN = 1b, I _O = 0 A, V _{VLNB} = 18.2 V | 1.5 | 5 | 8.5 | mA |
| | | V _{IN} rising | 4.15 | 4.3 | 4.45 | V |
| UVLO | V _{IN} undervoltage lockout | Hysteresis | 280 | 480 | 550 | mV |
| OUTPUT VC | DLTAGE | 1 - | | | | |
| | | V _(ctrl) = 1, I _O = 500 mA | 18 | 18.2 | 18.4 | V |
| | | V _(ctrl) = 0, I _O = 500 mA | 13.25 | 13.4 | 13.55 | V |
| V _{OUT} | Regulated output voltage | SCL = 1b, V _(ctrl) = 1, I _O = 500 mA (Non I ² C) | 19.18 | 19.4 | 19.62 | V |
| | | SCL = 1b, V _(ctrl) = 0, I _O = 500 mA (Non I ² C) | 14.44 | 14.6 | 14.76 | V |
| | | R _(SET) = 200 kΩ, Full temperature | 580 | 650 | 720 | mA |
| I _(OCP) | Output short circuit current limit | T _J = 25°C | 629 | 650 | 688 | mA |
| f _{SW} | Boost switching frequency | f = 1 MHz | 977 | 1060 | 1134 | kHz |
| I _(limitsw) (1) | Switching current limit | V_{IN} = 12 V, V_{OUT} = 18.2 V, $R_{(SET)}$ = 200 $k\Omega$ | | 3 | | Α |
| R _{ds(on)_LS} | On resistance of low side FET | V _{IN} = 12 V | 90 | 140 | 210 | mΩ |
| | | I _O = 500 mA, TONEAMP = 0b | 0.44 | 0.8 | 1.15 | V |
| $V_{(drop)}$ | Linear regulator voltage dropout | I _O = 500 mA, TONEAMP = 1b | 0.55 | 0.9 | 1.2 | V |
| I _(cable) | Cable good detection current threshold | V _{IN} = 12 V, V _{OUT} = 13.4 V or 18.2 V | 0.9 | 5 | 8.8 | mA |
| I _(rev) | Reverse bias current | EN = 1b, V _{VLNB} = 21 V | 49 | 58 | 65 | mA |
| I _(rev_dis) | Disabled reverse bias current | EN = 0b, V _{VLNB} = 21 V | 2.9 | 4.6 | 6.3 | mA |
| LOGIC SIGN | NALS | | | | | |
| | Enable threshold (V _(EN)), high | | 1.6 | | | V |
| | Enable threshold (V _(EN)), low | | | | 0.8 | V |
| | Foods internal culture consent | V _(EN) = 1.5 V | 5 | 6 | 7 | μA |
| I _(EN) | Enable internal pullup current | V _(EN) = 1 V | 2 | 3 | 4 | μA |
| V _(VCTRL_H) | VCTRL logic threshold level for high-level input voltage | | 2 | | | V |
| V _(VCTRL_L) | VCTRL logic threshold level for low-level input voltage | | | | 0.8 | V |
| V _(EXTM_H) | EXTM logic threshold level for high-level input voltage | | 2 | | | V |
| V _(EXTM_L) | EXTM logic threshold level for low-level input voltage | | | | 0.8 | V |
| V _{OL(FAULT)} | FAULT output low voltage | FAULT open drain, I _{OL} = 1 mA | | | 0.4 | V |
| TONE | | | | | | |
| f _(tone) | Tone frequency | 22-kHz tone output | 20 | 22 | 24 | kHz |
| Δ | Tone amplitude | $0 \text{ mA} \le I_O \le 500 \text{ mA}, C_O = 100 \text{ nF},$ TONEAMP = 0b | 617 | 650 | 696 | mV |
| A _(tone) | ione ampiliuue | $0 \text{ mA} \le I_O \le 500 \text{ mA}, C_O = 100 \text{ nF},$ TONEAMP = 1b | 703 | 750 | 803 | mV |
| D _(tone) | Tone duty cycle | | 45% | 50% | 55% | |
| _ | External tone input frequency range | 22-kHz tone output | 17.6 | 22 | 26.4 | kHz |
| † _(EXTM) | External tone input frequency range | 44-kHz tone output | 35.2 | 44 | 52.8 | kHz |



-40°C \leq T_J \leq 125°C, V_{IN} = 12 V, f_{SW} = 1 MHz (unless otherwise noted)

| | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-------------------------|---------------------------------------|--|-------|--------|-------|------|
| TONE DET | ECTION | | | | | |
| f _(DIN) | Tone detector frequency capture range | 0.4-V _{PP} sine wave | 17.6 | 22 | 26.4 | kHz |
| V _(DIN) | Tone detector input amplitude | Sine wave, 22 kHz | 0.3 | | 1.5 | V |
| V _(DOUT) | DOUT output voltage | Tone present, I _{load} = 2 mA | | | 0.4 | V |
| CDD | Dimensi FET and walkers I ND | TONE_TRANS = 1b, V _(LNB) = 18.2 V | 23.11 | 23.5 | 24.33 | V |
| GDR | Bypass FET gate voltage, LNB | TONE_TRANS = 0b, V _(LNB) = 18.2 V | 18.17 | 18.2 | 18.23 | V |
| THERMAL | SHUT-DOWN (JUNCTION TEMPERATURE |) | | | ' | |
| T _(TRIP) | Thermal protection trip point | Temperature rising | | 160 | | °C |
| T _(HYST) | Thermal protection hysteresis | | | 20 | | °C |
| I ² C READ I | BACK FAULT STATUS | | | | ' | |
| | D) PGOOD trip levels | Feedback voltage UVP low | 94% | 96% | 97.1% | |
| | | Feedback voltage UVP high | 93% | 94.5% | 95.5% | |
| $V_{(PGOOD)}$ | | Feedback voltage OVP high | 104% | 106.6% | 108% | |
| | | Feedback voltage OVP low | 102% | 104.6% | 106% | |
| T _(warn) | Temperature warning threshold | | | 125 | | °C |
| I ² C INTERF | ACE | | | | ' | |
| V _{IH} | SDA,SCL input high voltage | | 2 | | | V |
| V _{IL} | SDA,SCL input low voltage | | | | 0.8 | V |
| I _I | Input current | SDA, SCL, 0.4 V ≤ V _I ≤ 4.5 V | -10 | | 10 | μA |
| V _{OL} | SDA output low voltage | SDA open drain, I _{OL} = 2 mA | | | 0.4 | V |
| f _(SCL) | Maximum SCL clock frequency | | 400 | | | kHz |

(1) Specified by design



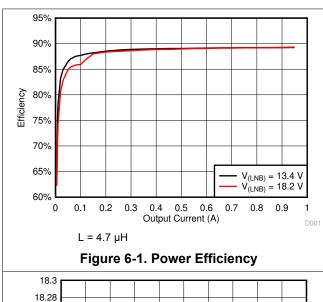
6.6 Timing Requirements

| | | | MIN | NOM | MAX | UNIT |
|---------------------------------|---|--|-------------------------|------|-------|------|
| OUTPUT V | /OLTAGE | | | | | |
| t _r , t _f | 13-V to 18-V transition rising falling time | C _(TCAP) = 22 nF | | 2 | | ms |
| t _{ON(min)} | Minimum on time for the Low side FET | | 75 | 102 | 130 | ns |
| TONE | | | | | | |
| | Tone rise time | 0 mA ≤ I _O ≤ 500 mA, C _O = 100 nF, Control Reg1[0] = 0b | | 11 | | μs |
| t _{r(tone)} | | 0 mA \leq I _O \leq 500 mA, C _O = 100 nF, Control Reg1[0] = 1b, and EXTM has 44-kHz input | | 5.5 | | μs |
| | Tone fall time | 0 mA ≤ I _O ≤ 500 mA, C _O = 100 nF, Control Reg1[0] = 0b | | 10.8 | | μs |
| t _{f(tone)} | | 0 mA \leq I _O \leq 500 mA, C _O = 100 nF, Control Reg1[0] = 1b, and EXTM has 44 kHz input | | 5.4 | | μs |
| OVERCUR | RENT PROTECTION | | | | • | |
| t _{ON} | Overcurrent protection ON time | TIMER = 0b | 2.3 | 3.75 | 5.52 | ms |
| t _{OFF} | Overcurrent protection OFF time | TIMER = 0b | 98.5 | 118 | 133.5 | ms |
| I ² C INTER | FACE | | | | - | |
| t _{BUF} | Bus free time between a STOP and START condition | | 1.3 | | | μs |
| t _{HD_STA} | Hold time (repeated) START condition | | 0.6 | | | μs |
| t _{su_sto} | Setup time for STOP condition | | 0.6 | | | μs |
| t _{LOW} | LOW period of the SCL clock | | 1 | | | μs |
| t _{HIGH} | HIGH period of the SCL clock | | 0.6 | | | μs |
| t _{SU_STA} | Setup time for a repeated START condition | | 0.6 | | | μs |
| t _{SU_DAT} | Data setup time | | 0.1 | | | μs |
| t _{HD_DAT} | Data hold time | | 0 | | 0.9 | μs |
| t _{RCL} | Rise time of SCL signal | Capacitance of one bus line (pF) | 20 + 0.1 C _B | | 300 | ns |
| t _{RCL1} | Rise time of SCL Signal after a Repeated START condition and after an acknowledge BIT | Capacitance of one bus line (pF) | 20 + 0.1 C _B | | 300 | ns |
| t _{FCL} | Fall time of SCL signal | Capacitance of one bus line (pF) | 20 + 0.1 C _B | | 300 | ns |
| t _{RDA} | Rise time of SDA signal | Capacitance of one bus line (pF) | 20 + 0.1 C _B | | 300 | ns |
| t _{FDA} | Fall time of SDA signal | Capacitance of one bus line (pF) | 20 + 0.1 C _B | | 300 | ns |
| Св | Capacitance of one bus line(SCL and SDA) | | | | 400 | pF |



6.7 Typical Characteristics

 $T_A = 25$ °C, $V_{IN} = 12$ V, $f_{SW} = 1$ MHz, $C_{Boost} = (2 \times 22 \mu F / 35 V)$ (unless otherwise noted)



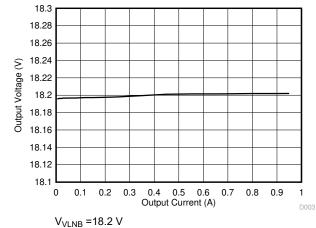


Figure 6-3. Load Regulation

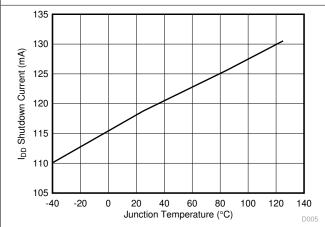


Figure 6-5. Shutdown Current vs Junction Temperature

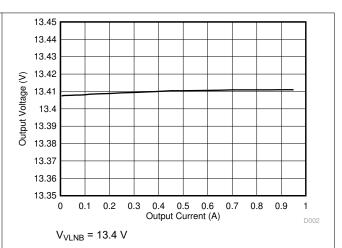


Figure 6-2. Load Regulation

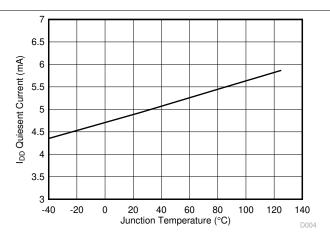


Figure 6-4. Input Supply Quiescent Current vs Junction Temperature

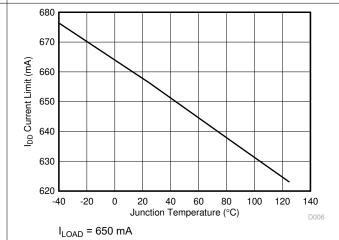


Figure 6-6. LNB Current Limit vs Junction Temperature



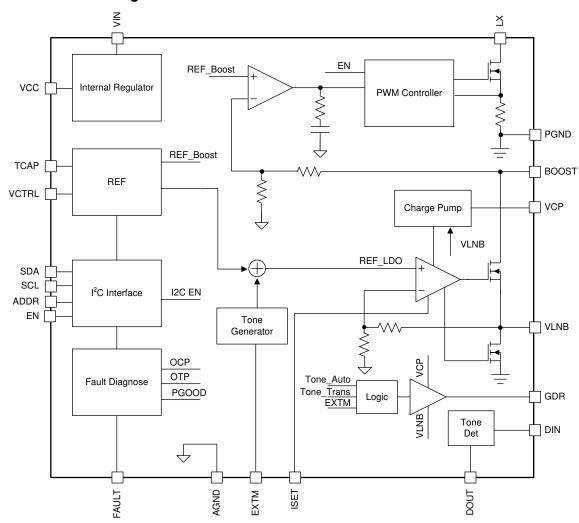
7 Detailed Description

7.1 Overview

The TPS65235-1 device is the power management IC (PMIC) that integrates a boost converter, an LDO regulator, and a 22-kHz tone generator to serve as a LNB power supply. This solution compiles the DiSEqC 2.x standard with or without I^2C interface. An external resistor allows for precise programming of the output current limit. The 22-kHz tone signal can be generated in one of two ways, either with or without I^2C . The integrated boost features low $R_{ds(on)}$ MOSFET and internal compensation. A selectable switching frequency of 1 MHz or 500 kHz is designed to reduce the size of passive components and be flexible for design.

The TPS65235-1 device can support the 44-kHz tone output. When the EXTM pin has a 44-kHz tone input, and the EXTM TONE bit in the *Control Register 1* is set to 1b, the LNB tone output is 44 kHz. By default, the TPS65235-1 device has a typical 22-kHz tone output.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Boost Converter

The TPS65235-1 device has an internal compensated boost converter and low-dropout (LDO) linear regulator. The boost converter tracks the LNB output voltage within 800 mV even at loading 1000 mA, which minimizes power loss.

The boost converter operates at 1 MHz by default. The TPS65235-1 device has internal cycle-by-cycle peak current limit in the boost converter and DC current limit in the LNB output to help protect the device from short

circuits and over loading. When the LNB output is shorted to ground, the LNB output current is clamped at the LDO current limit. The LDO current limit is set by the external resistor at the ISET pin. The current limit of the boost switch is proportional to the LDO current limit. If an overcurrent condition occurs for more than 4 ms, the boost converter enters hiccup mode and retries startup in 128 ms. This hiccup mode ON time and OFF time are selectable through the I^2 C control register (address 0x01) to be either 4 ms and 128 ms or 8 ms and 256 ms, respectively. At extremely light loads, the boost converter automatically operates in a pulse-skipping mode.

The boost converter is stable with either ceramic capacitor or electrolytic capacitor.

If two or more set-top box LNB outputs are connected together, one output voltage can be set higher than others. The output with the lower set voltage is then effectively turned off. When the voltage drops to the set level, the LNB output with the lower set output voltage returns to normal conditions.

7.3.2 Linear Regulator and Current Limit

The linear regulator is used to generate the 22-kHz tone signal by changing the LDO reference voltage. The linear regulator features low-dropout voltage to minimize power loss while maintaining enough head room for the 22-kHz tone with 650-mV amplitude. The linear regulator also implements a tight current limit for overcurrent protection. The current limit is set by an external resistor connected to ISET pin. Figure 7-1 shows the relationship between the current limit threshold and the resistor value.

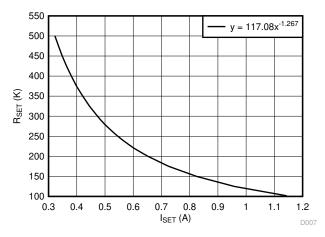


Figure 7-1. Linear Regulator Current Limit Vs Resistor

$$R_{SET}(k\Omega) = 117.08 \times I_{SET}^{-1.267}(A)$$
 (1)

A 200-k Ω resistor sets the current to 0.65 A, and 110-k Ω resistor sets the current to approximately 1 A.



7.3.3 Boost Converter Current Limit

The boost converter has the cycle-by-cycle peak current limit on the internal Power MOSFET switch to serve as the secondary protection when LNB output is hard short. With ISW bit default setting 0b on I^2C control register 0x01, the switch current limit I_{SW} is proportional as LDO current limit $I_{(OCP)}$ set by ISET pin resistor, and the relationship can be expressed as:

$$I_{SW} = 3 \times I_{(OCP)} + 0.8 A$$
 (2)

For the 5 V V_{IN} , if LNB current load is up to 1 A, the ISW bit must be written as 1b, the switch current limit I_{SW} for the internal Power MOSFET is:

$$I_{SW} = 5 \times I_{(OCP)} + 0.8 A$$
 (3)

While due to the high power loss at 5 V, V_{IN}, it has a chance to trigger the thermal shutdown before the loading is up to 1 A, especially the VLNB output is high.

7.3.4 Charge Pump

The charge pump circuitry generates a voltage to drive the NMOS of the linear regulator. The voltage across the charge pump capacitor between VLNB and VCP is about 5.4 V, so the absolute value of the VCP voltage will be VLNB + 5.4 V.

7.3.5 Slew Rate Control

When LNB output voltage transits from 13.4 V to 18.2 V or 18.2 V to 13.4 V, the cap at pin TCAP controls the transition time. This transition time makes sure the boost converter output to follow LNB output change. Usually boost converter has low bandwidth and can't response fast. The voltage at TCAP acts as the reference voltage of the linear regulator. The boost converter's reference is also based on TCAP with additional fixed voltage to generate a 0.8 V above the LNB output.

The charging and discharging current is 10 µA, thus the transition time can be estimated as:

$$t_{TCAP} (ms) = 0.8 \times \frac{C_{SS} (nF)}{I_{SS} (\mu A)}$$
 (4)

A 22-nF capacitor generates about 2 ms transition time.

In light load conditions, when LNB output voltage is set from 18.2 V to 13.4 V, the voltage drops very slow, which causes wrong VOUT_GOOD (Bit 0 at status register 0x02) logic for LNB output voltage detection. TPS65235-1 has integrated a pull down circuit to pull down the output during the transition. This ensures the voltage change can follow the voltage at TCAP. When the 22-kHz tone signal is superimposing on the LNB output voltage, the pull down current can also provide square wave instead of a distorted waveforms.

7.3.6 Short-Circuit Protection, Hiccup, and Overtemperature Protection

The LNB output current limit can be set by an external resistor. When short circuit conditions occur or current limit is triggered, the output current is clamped at the current limit for 4 ms with LDO on. If the condition retains, the converter will shut down for 128 ms and then restart. This hiccup behavior prevents IC from being overheat. The hiccup ON/OFF time can be set by I²C register. Refer to *Control Register 1* for detail.

The low side MOSFET of the boost converter has a peak current limit threshold which serves as the secondary protection. If boost converter's peak current limit is triggered, the peak current will be clamped as high as 3.8 A when setting I_{SW} default and LNB current limit up to 1 A. If loading current continues to increase, output voltage starts to drop and output power drops.

Thermal shutdown prevents the chip from operating at exceedingly high temperatures. When the junction temperature exceeds 160°C, the output shuts down. When the die temperature drops below its lower threshold typically 140°C, the output is enabled.

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When the chip is in overcurrent protection or thermal shutdown, the I²C interface and logic are still active. The FAULT pin is pulled down to signal the processor. The FAULT pin signal remains low unless the following action

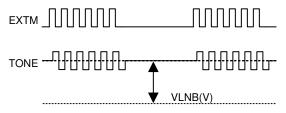
- 1. If I²C interface is not used to control, EN pin must be recycled to pull the FAULT pin back to high.
- 2. If I²C interface is used, the I²C controller must read the status *Control Register 2*, then the FAULT pin is back

7.3.7 Tone Generation

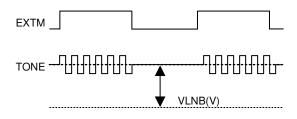
A 22-kHz tone signal is implemented at the LNB output voltage as a carrier for DiSEqC command. This tone signal can be generated by feeding an external 22-kHz clock at the EXTM pin, and it can also be generated with its internal tone generator controlled by EXTM pin. If EXTM pin is toggled to high, the internal tone signal will be superimposed at the LNB output, if EXTM pin is low, there will be no tone superimposed at the output stage of the regulator facilitates a push-pull circuit, so even at zero loading; the 22-kHz tone at the output is still clean without distortion.

There are two ways to generate the 22-kHz tone signal at the output.

For option1, if the EXTM has 44-kHz tone input, and the bit EXTM TONE of the Control Register 1 is set to 1b, the LNB tone output is 44 kHz.



Option 1. Use external tone, gated by EXTM logic pulse



Option 2. Use internal tone, gated by EXTM logic envelop

Figure 7-2. Two Ways to Generate 22-kHz tone

7.3.8 Tone Detection

A 22-kHz tone detector is implemented in the TPS65235-1 solution. The detector extracts the AC-coupled tone signal from the DIN input and provides it as an open-drain signal on the DOUT pin. When the DOUTMODE bit in the Control Register 2 is set to the default setting, if a tone is present, the DOUT output is logic low. If a tone is not present, the internal output FET is off. If a pullup resistor is connected to the DOUT pin, the output is logic high. The maximum tone out delay with respect to the input is one and a half of the tone cycle.

The DOUTMODE bit in the Control Register 2 is reserved and must not be used.



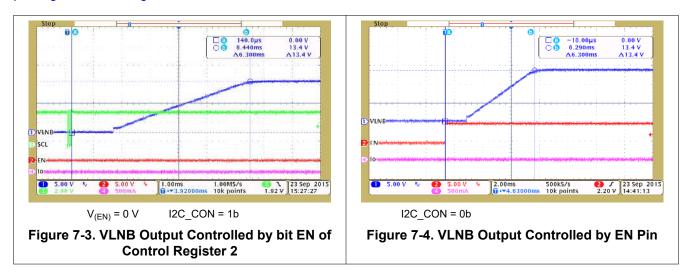
7.3.9 Audio Noise Rejection

When the TPS65235-1 operates in PSM mode, locating the switching frequency at the range of audio frequency is possible. Which causes audible noise, especially when the VLNB voltage is lower or closer to the VIN voltage, and the current load is light.

When audible noise occurs, TI recommends setting the TPS65235-1 device to operate in force PWM mode. In force PWM mode, a special design is implemented to avoid the audible noise.

7.3.10 Disable and Enable

The TPS65235-1 device has a dedicated EN pin to disable and enable the LNB output. In a non-I²C application, when the EN pin is pulled high, the LNB output is enabled. When the EN pin is pulled low, the LNB output is disabled. In an I²C application, when the EN pin is either low or high, the I²C registers can be accessed, which allows users to change the default LNB output at system power-up. When the I2C_CON bit in the *Control Register 1* is set to 1b, the LNB output enable or disable is controlled by the EN bit in the *Control Register 2*. By default, the I2C_CON bit of the control register is set to 0b, which makes the LNB output is controlled by the EN pin. Figure 7-3 and Figure 7-4 shows the detailed control behavior.



7.3.11 Component Selection

7.3.11.1 Boost Inductor

TI recommends the TPS65235-1 device to operate with a boost inductor value of 4.7 μ H or 10 μ H. The boost inductor must be able to support the peak current requirement to maintain the maximum LNB output current without saturation. Use Equation 5 to estimate the peak current of the boost inductor (I_{peak}).

$$I_{\text{peak}} = \frac{I_{\text{OUT}}}{1 - D} + \frac{1}{2} \times \frac{V_{\text{IN}} \times D}{L \times f_{\text{S}}}$$
 (5)

where

$$D = 1 - \frac{V_{IN}}{VLNB + 0.8}$$

With a different inductance, the system has different gain and phase margins. Figure 7-5 shows a Bode plot of boost loop with 2 × 10 μ F / 35 V of boost capacitor and 4.7 μ H, 5.6 μ H, 6.8 μ H, 8.2 μ H, and 10 μ H of boost inductance. As the boost inductance increases, the 0-dB crossover frequency keeps relatively constant while reducing the phase and gain margins. With a 4.7- μ H boost inductance, the phase margin is 66.96° and with a 10- μ H inductance, the phase margin is 39.63°.

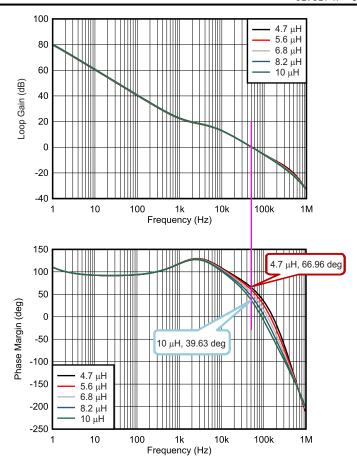


Figure 7-5. Gain and Phase Margin of the Boost Loop with Different Inductance (V_{IN} = 12 V, V_{OUT} = 18.2 V, I_{LOAD} = 1 A, f_{SW} = 1 MHz, 5 μ F, Typical Bode Plot)

7.3.11.2 Capacitor Selection

The TPS65235-1 device has a 1-MHz nonsynchronous boost converter integrated and the boost converter features the internal compensation network. The TPS65235-1 device works well with both ceramic capacitor and electrolytic capacitor.

The recommended ceramic capacitors for the TPS65235-1 application are, at the minimum, rated as X7R/X5R, with a 35-V rating, and a 1206 size for the achieving lower LNB output ripple. Table 7-1 lists the recommended ceramic capacitors list for both $4.7-\mu H$ and $10-\mu H$ boost inductors.

If more cost-effictive design is needed, use a $100-\mu F$ electrolytic (low ESR) and a $10-\mu F$ or 35-V ceramic capacitor.

Table 7-1. Boost Inductor and Capacitor Selections

| BOOST INDUCTOR | CAPACITORS | TOLERANCE (%) | RATING (V) | SIZE |
|----------------|------------|---------------|------------|------|
| 10 μH | 2 × 22 μF | ±10 | 35 | 1206 |
| το μιτ | 2 × 10 μF | ±10 | 35 | 1206 |
| | 2 × 22 μF | ±10 | 35 | 1206 |
| 4.7 µH | 2 × 10 μF | ±10 | 35 | 1206 |
| | 22 µF | ±10 | 35 | 1206 |

Figure 7-6 and Figure 7-7 show a bode plot of boost loop with 4.7- μ H and 10- μ H inductance and 4 μ F, 5 μ F, 7.5 μ F, 10 μ F, 15 μ F, and 20 μ F of boost capacitance after degrading. As the boost capacitance increases, the phase margin increases.

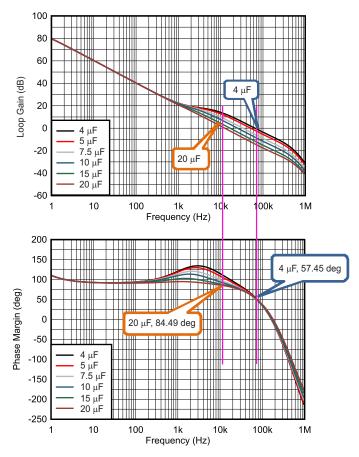


Figure 7-6. Gain and Phase Margin of the Boost Loop With Different Boost Capacitance (V_{IN} = 12 V, V_{OUT} = 18.2 V, I_{LOAD} = 1 A, f_{SW} = 1 MHz, 4.7 μ H, Typical Bode Plot)

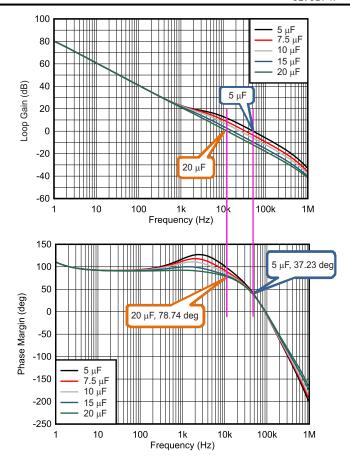


Figure 7-7. Gain and Phase Margin of the Boost Loop With Different Boost Capacitance (V_{IN} = 12 V, V_{OUT} = 18.2 V, I_{LOAD} = 1 A, f_{SW} = 1 MHz, 10 μ H, Typical Bode Plot)

7.3.11.3 Surge Components

If a surge test is required for the application, the D0 and D2 diodes must be added as the external protection components. If no surge test is required, remove the D0 and D2 diodes. Table 7-2 lists the recommended surge components.

Table 7-2. Surge Components

| DESIGNATOR | DESCRIPTION | PART NUMBER | MANUFACTURER (1) |
|------------|------------------------------------|-------------|-------------------------|
| D0 | Diode, TVS, Uni, 28 V, 1500 W, SMC | SMCJ28A | Fairchild Semiconductor |
| D2 | Diode, Schottky, 40 V, 2 A, SMA | B240A-13-F | Diodes Inc. |

(1) See Third-party Products Disclaimer

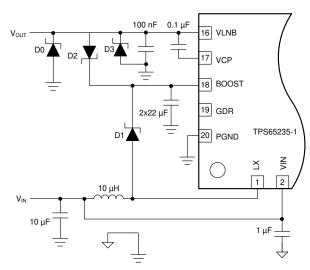


Figure 7-8. Surge Components Selection

7.3.11.4 Consideration for Boost Filtering and LNB Noise

Smaller capacitance on the BOOST pin reduces the cost of the system. However, when the inductor in system is the same, the smaller capacitance on the boost and the larger ripple on the LNB output.

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7.4 Device Functional Modes

Table 7-3 is the logic table for the device.

Table 7-3. Logic table

| EN | I2C_CON ⁽¹⁾ (2) (3) | SCL | VCTRL | VLNB ⁽⁴⁾ |
|----|--------------------------------|-----|-------|---|
| Н | 0 | Н | Н | 19.4 V |
| Н | 0 | Н | L | 14.6 V |
| Н | 0 | L | Н | 18.2 V |
| Н | 0 | L | L | 13.4 V |
| Х | 1 | X | X | Controlled by VSET[3:0] bits at 0x01 register ⁽⁵⁾ |
| L | 0 | X | X | 0 V |

- $I2C_CON$ is the bit7 of the I^2C control register 0x01, which is used to set the VLNB output controlled by the I^2C register or not. When I^2C interface is used in design, all the I^2C registers are accessible even if the I^2C_CON bit is 0b. (1)
- (2)
- When I2C_CON is 1b, the VLNB output is controlled by the I²C control register even if the EN pin is low. (3)
- When I²C interface is used in design, TI recommends to set the I2C_CON with 1b, if not, the LNB output will be variable because the SCL is toggled by the I²C register access as the clock signal.
- Bit EN of the control register2 is used to disable or enable the LNB output, by default, the bit EN is 1b which enable the LNB output

7.5 Programming

7.5.1 Serial Interface Description

I²C is a 2-wire serial interface developed by Philips Semiconductor (see I²C-Bus Specification, Version 2.1, January 2000). The bus consists of a data line (SDA) and a clock line (SCL) with pullup structures. When the bus is idle, both SDA and SCL lines are pulled high external. All the I²C compatible devices connect to the I²C bus through open drain I/O pins, SDA and SCL. A controller device, usually a microcontroller (MCU) or a digital signal processor (DSP), controls the bus. The controller device is responsible for generating the SCL signal and device addresses. The controller device also generates specific conditions that indicate the START and STOP of data transfer. A target device receives, transmits data, or both on the bus under control of the controller device.

The TPS65235-1 device works as a target and supports the following data transfer modes, as defined in the I²CBus Specification: standard mode (100 kbps), and fast mode (400 kbps). The interface adds flexibility to the power supply solution, enabling most functions to be programmed to new values depending on the instantaneous application requirements. Register contents remain intact as long as supply voltage remains above 4.5 V (typical).

The data transfer protocol for standard and fast modes is exactly the same; therefore, they are referred to as F/S-mode in this document. The TPS65235-1 device supports 7-bit addressing; 10-bit addressing and general call address are not supported.

The TPS65235-1 device has a 7-bit address set by ADDR pin. Table 7-4 shows how to set the I²C address.

Table 7-4. I²C Address Selection

| ADDR PIN | I ² C ADDRESS | ADDRESS FORMAT (A6 ≥ A0) |
|--|--------------------------|--------------------------|
| Connect to VCC | 0x08 | 000 1000Ь |
| Floating | 0x09 | 000 1001b |
| Connected to GND | 0x10 | 001 0000Ь |
| Resistor divider to make ADDR pin voltage in 3.7 V - 5.9 V | 0x11 | 001 0001b |

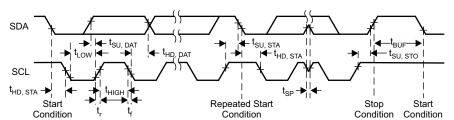


Figure 7-9. I²C Interface Timing Diagram



7.5.2 TPS65235-1 I²C Update Sequence

The TPS65235-1 requires a start condition, a valid I²C address, a register address byte, and a data byte for a single update. After the receipt of each byte, TPS65235-1 device acknowledges by pulling the SDA line low during the high period of a single clock pulse. TPS65235-1 performs an update on the falling edge of the LSB byte.

When the TPS65235-1 is disabled (EN pin tied to ground) the device cannot be updated via the I²C interface.

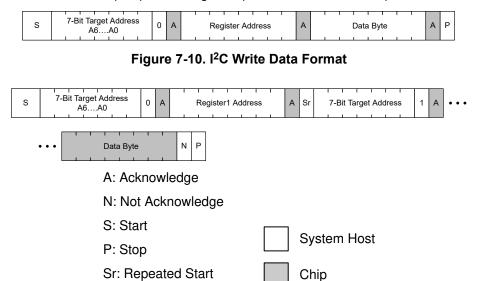


Figure 7-11. I²C Read Data Format



7.6 Register Maps

7.6.1 Control Register 1 (address = 0x00) [reset = 0x08]

Figure 7-12. Control Register 1

| 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|---------|---------|----------|---|-------|--------|---|-----------|
| I2C_CON | PWM/PSM | RESERVED | | VSET | Γ[3:0] | | EXTM TONE |
| R/W-0b | R/W-0b | R/W-0b | | R/W-0 | 0100b | | R/W-0b |

Table 7-5. Control Register 1

| Bit | Field | Туре | Reset | Description |
|-----|-----------|------|-------|--|
| 7 | I2C_CON | R/W | 0b | 0b = I ² C control disabled 1b = I ² C control enabled |
| 6 | PWM/PSM | R/W | 0b | 0b = PSM at light load 1b = Forced PWM |
| 5 | RESERVED | R/W | 0b | Reserved |
| 4-1 | VSET[3:0] | R/W | 0100b | LNB output voltage selection 0000b = 11 V 0001b = 11.6 V 0010b = 12.2 V 0011b = 12.8 V 0100b = 13.4 V 0101b = 14 V 0110b = 14.6 V 0111b = 15.2 V 1000b = 15.8 V 1001b = 16.4 V 1010b = 17 V 1011b = 17.6 V 1100b = 18.2 V 1101b = 18.8 V 1110b = 19.4 V 1111b = 20 V |
| 0 | EXTM TONE | R/W | 0b | 0b = EXTM 44-kHz tone input not support, with only 22-kHz tone output at VLNB 1b = EXTM 44-kHz tone input support, with 44-kHz tone output at VLNB |

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7.6.2 Control Register 2 (address = 0x01) [reset = 0x09]

Figure 7-13. Control Register 2

| | | | • | | | | |
|---------|--------|-----------------|--------|--------|----------|-----------|------------|
| 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
| TONEAMP | TIMER | I _{sw} | FSET | EN | DOUTMODE | TONE_AUTO | TONE_TRANS |
| R/W-0b | R/W-0b | R/W-0b | R/W-0b | R/W-1b | R/W-0b | R/W-0b | R/W-1b |

Table 7-6. Control Register 2

| | · · · | | | negister 2 |
|-----|------------|------|-------|--|
| Bit | Field | Туре | Reset | Description |
| 7 | TONEAMP | R/W | 0b | 0b = 22-kHz tone amplitude is 650 mV (typ) 1b = 22-kHz tone amplitude is 750 mV (typ) |
| 6 | TIMER | R/W | 0b | 0b = Hiccup ON time set to 4 ms and OFF time set to 128 ms 1b = Hiccup ON time set to 8 ms and OFF time set to 256 ms |
| 5 | Isw | R/W | 0b | 0b = Boost switch peak current limit set to 3 × I _{OCP} + 0.8 A 1b = Boost switch peak current limit set to 5 × I _{OCP} + 0.8 A |
| 4 | FSET | R/W | 0b | 0b = 1-MHz switching frequency 1b = 500-kHz switching frequency |
| 3 | EN | R/W | 1b | 0b = LNB output disabled 1b = LNB output voltage Enabled |
| 2 | DOUTMODE | R/W | 0b | 0b = DOUT is kept to low when DIN has the tone input 1b = Reserved, cannot set to 1b |
| 1 | TONE_AUTO | R/W | 0b | 0b = GDR (External bypass FET control) is controlled by TONE_TRANS 1b = GDR (External bypass FET control) is automatically controlled by 22-kHz tones transmit |
| 0 | TONE_TRANS | R/W | 1b | 0b = GDR output with VLNB voltage for tone receive. Bypass FET is OFF for tone receiving from satellite 1b = GDR output with VCP voltage. Bypass FET is ON for tone transmit from TPS65235-1 |

Table 7-7. 22-kHz Tone Receive Mode Selection

| TONE_AUTO | TONE_TRANS | BYPASS FET |
|-----------|------------|-------------|
| 0b | 0b | OFF |
| 0b | 1b | ON |
| 1b | x | Auto Detect |

The TPS65235-1 has full range of diagnostic flags for operation and debug. Processor can read the status register to check the error conditions. After the error happens, the flags are changed, once the errors are gone, the flags are set back without I²C access.

If the TSD and OCP flags are triggered, FAULT pin will be pulled low, so FAULT pin can be the interrupt signal to processor. After TSD and OCP are set to 1b, the FAULT pin logic is latched to low, processor must read this status register to release the fault conditions.



7.6.3 Status Register (address = 0x02) [reset = 0x29]

Figure 7-14. Status Register

| 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|----------|------|--------|------|------|------|------------|-----------|
| Reserved | 0 | LDO_ON | T125 | TSD | OCP | CABLE_GOOD | VOUT_GOOD |
| R-0b | R-0b | R-0b | R-0b | R-1b | R-0b | R-0b | R-1b |

Table 7-8. Status Register

| Bit | Field | Туре | Reset | Description |
|-----|------------|------|-------|---|
| 7 | Reserved | R | 0b | Reserved |
| 6 | TDETGOOD | R | 0b | 0b = 22-kHz tone detected on DIN pin is out of range 1b = 22-kHz tone detected on DIN pin is in range |
| 5 | LDO_ON | R | 1b | 0b = Internal LDO is turned off but boost converter is on 1b = Internal LDO is turned on and boost converter is on |
| 4 | T125 | R | 0b | 0b = Die temperature < 125°C 1b = Die temperature > 125°C |
| 3 | TSD | R | 1b | 0b = No thermal shutdown triggered 1b = Thermal shutdown triggered. The FAULT pin logic is latched to low, processor must read this register to release the fault conditions |
| 2 | OCP | R | 0b | 0b = Overcurrent protection conditions released 1b = Overcurrent protection triggered. The FAULT pin logic is latched to low, processor must read this register to release the fault conditions |
| 1 | CABLE_GOOD | R | 0b | 0b = Cable not connected 1b = Cable connection good |
| 0 | VOUT_GOOD | R | 1b | 0b = LNB output voltage out of range 1b = LNB output voltage in range |

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8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers must validate and test their design implementation to confirm system functionality.

8.1 Application Information

The TPS65235 supports both DisEqc1.x and DisEqc2.x application. When the input voltage VIN is greater than the expected output voltage VLNB, the linear regulator drops the voltage difference between VIN and VLNB, which causes the lower efficiency and the higher power loss on the internal linear regulator if the current loading is high. For care must be taken to ensure that the safe operating temperature range of the TPS65235-1 is not exceeded. TI recommends operating the device in force PWM mode when $V_{\text{IN}} > V_{\text{OUT}}$ to reduce output ripple.

8.2 Typical Application

8.2.1 DiSEqc1.x Support

TPS65235-1 can operate in I²C and non-I²C interface mode. Figure 8-1 shows the application with the device in I²C interface mode to support DiSEqC 1.x application. In non-I²C mode, the SCL, SDA, and ADDR pins can be floating.

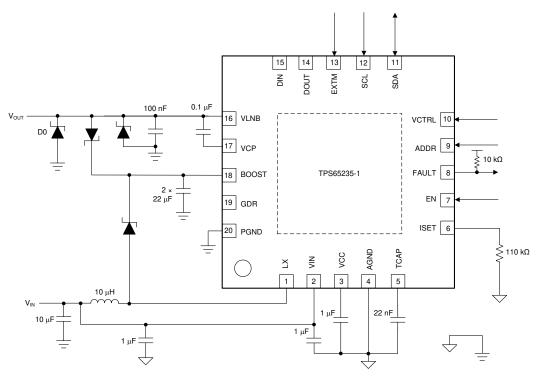


Figure 8-1. Application for DiSEqc1.x Support



8.2.1.1 Design Requirements

For this design example, use the parameters in Table 8-1.

Table 8-1. Design Parameters

| PARAMETER | VALUE |
|---------------------------------------|---------------|
| Input voltage range, V _{IN} | 4.5 V to 20 V |
| Output voltage range V _{LNB} | 11 V to 20 V |
| Output current range | 0 A to 1 A |

8.2.1.2 Detailed Design Procedure

To begin the design process, the following component values must be selected:

- Inductor
 - Choose the appropriate value of the inductor based on application cost requirements, ripple requirements, and Section 7.3.11.
- BOOST capacitor
 - Choose the appropriate BOOST capacitor value based on application cost requirements, ripple requirements, and Section 7.3.11.
- Diodes
 - The D0 and D2 diodes are used to help meet the surge-protection requirement of the application. If the
 application does not require surge protection, remove these diodes. For diode component selection, refer
 to Section 7.3.11.3.
 - The D1 diode is used for the boost loop. TI recommends a Schottky diode for D1. The application requirements, which include input power range, output power range, and the current requirement, determine the current and voltage capability of the D1 diode.
 - The D3 diode is to help with the output protection for the VLNB voltage. TI recommends a Schottky diode for D3. The application requirements determine the current and voltage capability of the D3 diode.

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8.2.1.3 Application Curves

 $T_A = 25$ °C, $V_{IN} = 12$ V, $f_{SW} = 1$ MHz, $C_{Boost} = (2 \times 22 \mu F / 35 V)$ (unless otherwise noted)

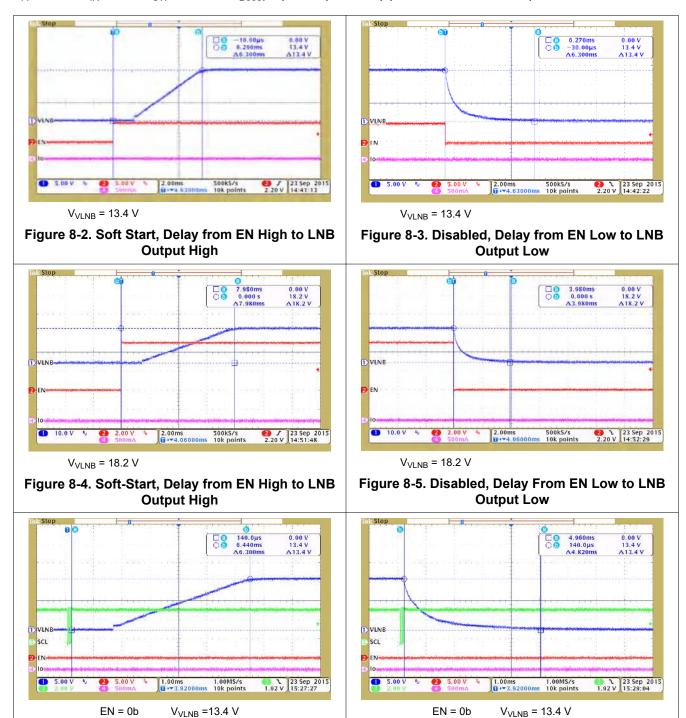


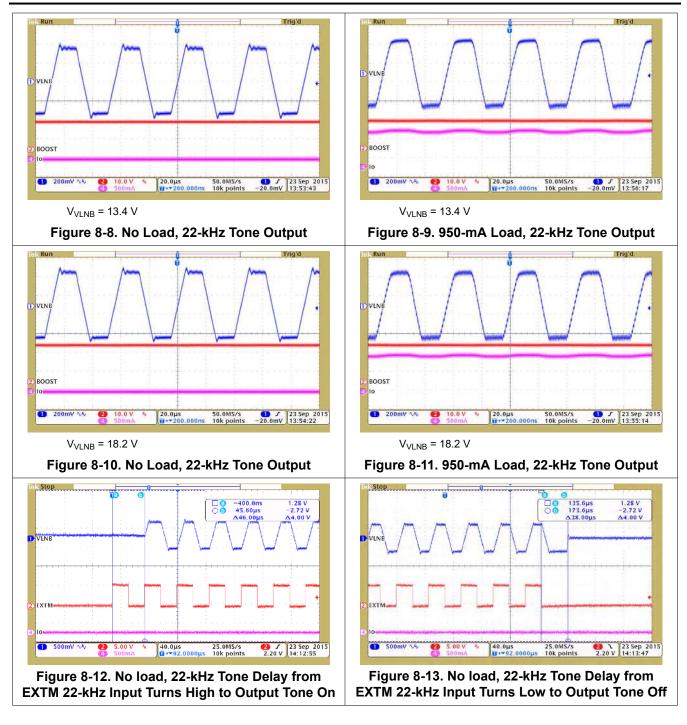
Figure 8-6. Soft Start, Delay From I²C Enable

(I2C_CON = 1b) to LNB Output High

Figure 8-7. Delay From I^2C Disable ($I2C_CON = 0b$)

to LNB Output Low





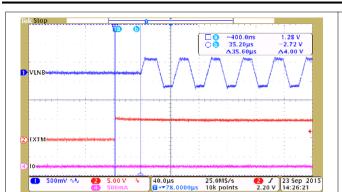


Figure 8-14. No Load, 22-kHz Tone Delay from EXTM Tone Envelop Input Turns High to Output Tone On

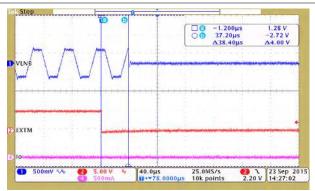


Figure 8-15. No Load, 22-kHz Tone Delay from EXTM Tone Envelop Input Turns Low to Output Tone Off

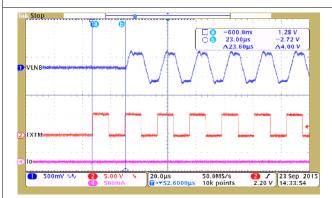


Figure 8-16. No Load, 44-kHz Tone Delay from EXTM 22-kHz Input Turns High to Output Tone On

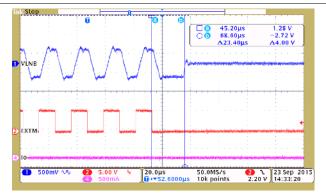


Figure 8-17. No Load, 44-kHz Tone Delay from EXTM 22-kHz Input Turns Low to Output Tone Off



8.2.2 DiSEqc2.x Support

The TPS65235-1 can support both DiSEqC 1.x application and DiSEqC 2.x application. Figure 8-18 shows the application for supporting DiSEqC 2.x application.

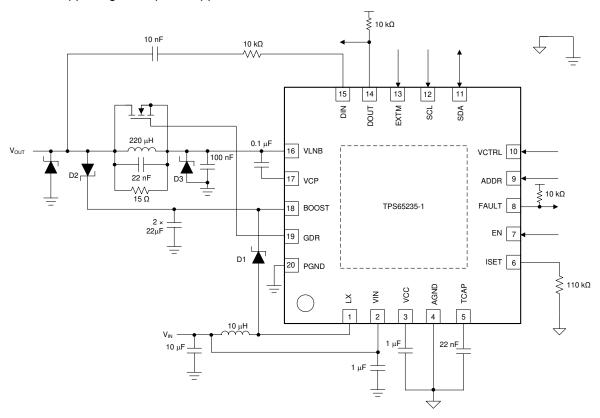


Figure 8-18. Application Schematic for DiSEqc2.x Support

8.2.2.1 Design Requirements

Refer to the Section 8.2.1 section for design requirements.

8.2.2.2 Detailed Design Procedure

Refer to the *Section 8.2.1* section for detailed design procedures.

8.2.2.3 Application Curve

Refer to the Section 8.2.1 section for typical application curves. Figure 8-19 is the unique tone-detection curve for the DiSEqC 2.x application.

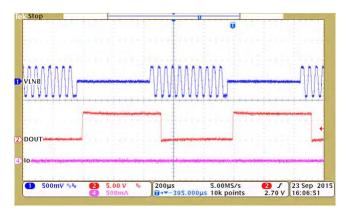


Figure 8-19. DOUT Tone Detection Output

8.3 Power Supply Recommendations

The device is designed to operate from an input supply ranging from 4.5 V to 20 V. The input supply must be well regulated. If the input supply is located more than a few inches from the converter, an additional bulk capacitance, typically with a value $100 \, \mu F$, can be required in addition to the ceramic bypass capacitors.

8.4 Layout

8.4.1 Layout Guidelines

The TPS65235-1 is designed to layout in 2-layer PCB. To ensure reliability of the device, TI recommends following common printed-circuit board layout guidelines.

- Make sure the ground of input capacitor, output capacitor, and the boost converter are connected at one point at same layer.
- The PGND and AGND pins are located in different regions. Connect these grounds to the thermal pad. Other components are connected the AGND pin.
- · Put the BOOST capacitors as close as possible.
- The loop from the VIN inductor to the LX pin must be as short as possible.
- The loop from the VIN inductor to D1 Schottky diode to the BOOST must be as short as possible.
- The loop for boost capacitors to the PGND pin must be within the loop from the LX pin to D1 Schottky diode to the BOOST pin.



8.4.2 Layout Example



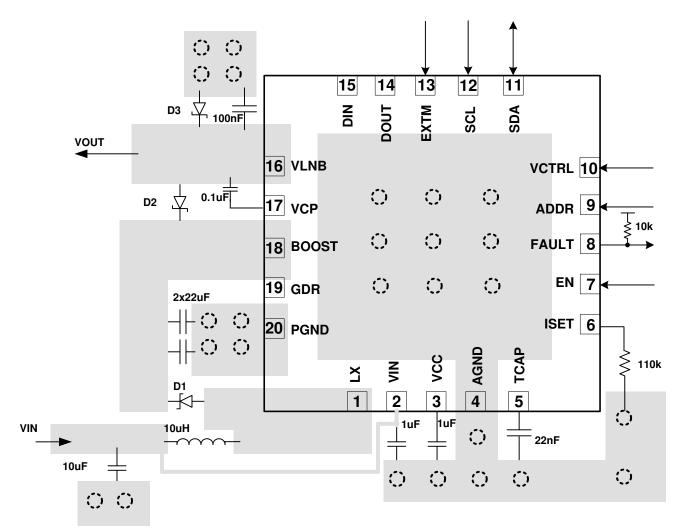


Figure 8-20. Layout



9 Device and Documentation Support

9.1 Device Support

9.1.1 Third-Party Products Disclaimer

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9.2 Documentation Support

9.2.1 Related Documentation

For related documentation see the following:

- Texas Instruments, Evaluation Module for the TPS65235-1 LNB Voltage Regulator With I²C Interface for DiSEqC2.x Application user's guide
- Texas Instruments, Evaluation Module for the TPS65235-1 LNB Voltage Regulator With I²C Interface for DiSEqC1.x Application user's guide

9.3 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.4 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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9.6 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.7 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.



10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



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PACKAGING INFORMATION

| Orderable Device | Status | Package Type | Package Drawing | Pins | Package Qty | Eco Plan | Lead finish/ Ball material | MSL Peak Temp | Op Temp (°C) | Device Marking (4/5) | Samples |
|------------------|--------|--------------|--------------------|------|----------------|--------------|-------------------------------|---------------------|--------------|-------------------------|---------|
| TPS65235-1RUKR | ACTIVE | WQFN | RUK | 20 | 3000 | RoHS & Green | NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | 652351 | Samples |
| TPS65235-1RUKT | ACTIVE | WQFN | RUK | 20 | 250 | RoHS & Green | NIPDAU | Level-2-260C-1 YEAR | -40 to 85 | 652351 | Samples |

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

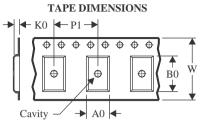
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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





| A0 | Dimension designed to accommodate the component width |
|----|---|
| В0 | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

| Device | Package Type | Package Drawing | | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|----------------|-----------------|--------------------|----|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| TPS65235-1RUKR | WQFN | RUK | 20 | 3000 | 330.0 | 12.4 | 3.3 | 3.3 | 1.1 | 8.0 | 12.0 | Q2 |
| TPS65235-1RUKR | WQFN | RUK | 20 | 3000 | 330.0 | 12.4 | 3.3 | 3.3 | 1.1 | 8.0 | 12.0 | Q2 |
| TPS65235-1RUKT | WQFN | RUK | 20 | 250 | 180.0 | 12.4 | 3.3 | 3.3 | 1.1 | 8.0 | 12.0 | Q2 |



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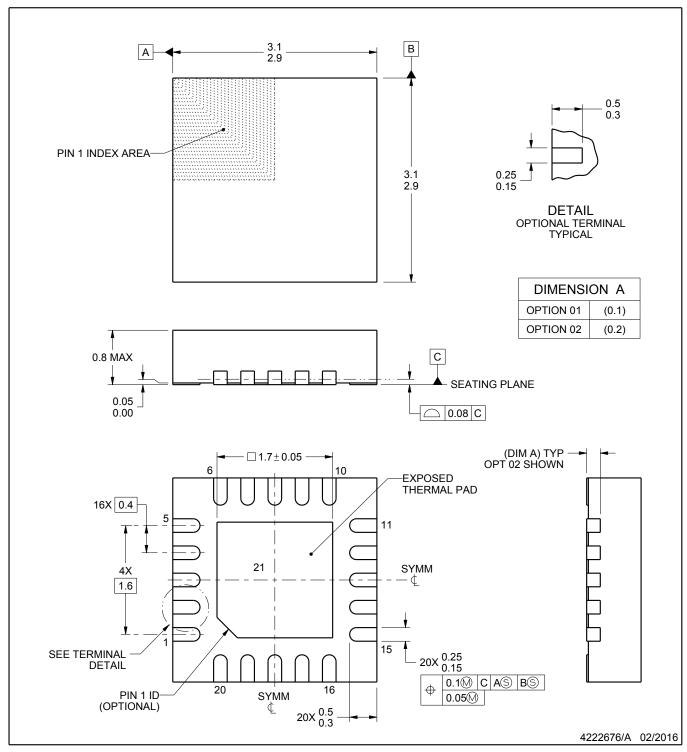


*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|----------------|--------------|-----------------|------|------|-------------|------------|-------------|
| TPS65235-1RUKR | WQFN | RUK | 20 | 3000 | 346.0 | 346.0 | 33.0 |
| TPS65235-1RUKR | WQFN | RUK | 20 | 3000 | 367.0 | 367.0 | 35.0 |
| TPS65235-1RUKT | WQFN | RUK | 20 | 250 | 210.0 | 185.0 | 35.0 |



PLASTIC QUAD FLATPACK - NO LEAD



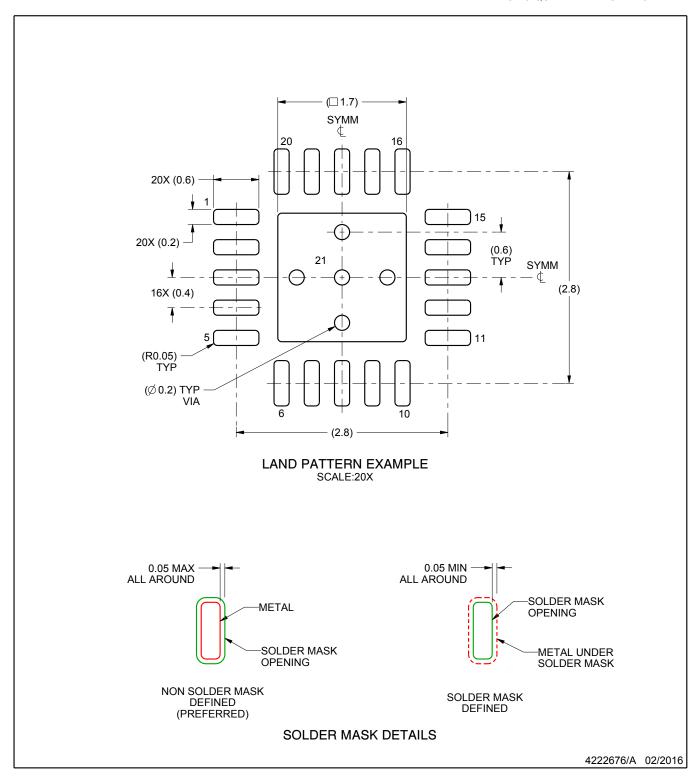
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD

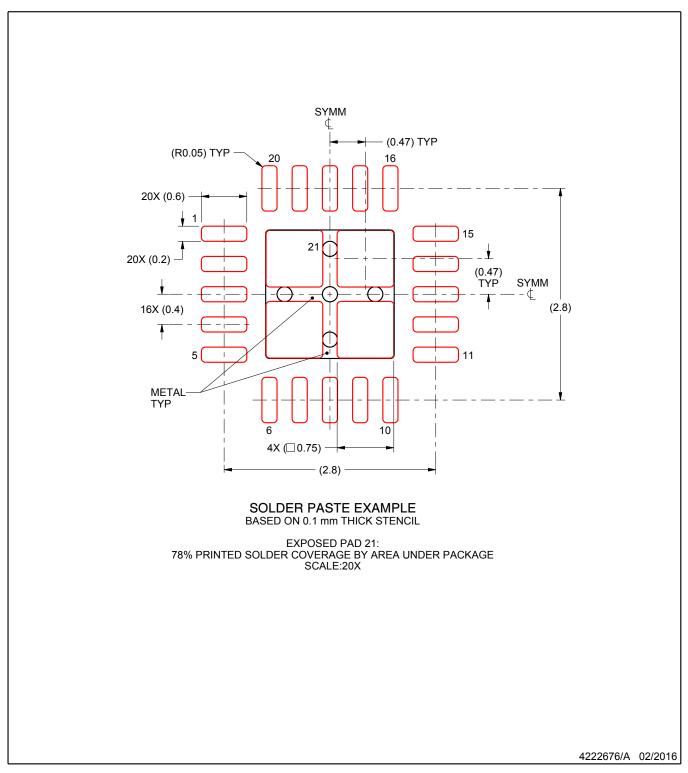


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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